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Application Number	10/671,233
Filing Date	09/25/03
First Named Inventor	Jian H. Zhao
Art Unit	
Examiner Name	Tan N. Tran
Attorney Docket Number	N/A

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		K. ASANO, et. al, 5kV 4H-SiC SEJFET with Low RonS of 69 m-ohm-cm2, Proc. of 14th Intl. Symp. on Power Semiconductor Devices & IC 2002, June 3, 2002,	
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		Jian H. Zhao, et al., Demonstration of a high performance 4H-SiC vertical junction field effect transistor without epitaxial regrowth, Feb. 2003, pp. 321-323,	
		Electronics Letters, IEE, Stevenage, SG1 2SD, UK.	

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